Michelle Y Simmons

List of Publications by Citations

331 papers	9,566 citations	46 h-index	85 g-index
354 ext. papers	10,626 ext. citations	5.8 avg, IF	5.74 L-index

#	Paper	IF	Citations
331	Silicon quantum electronics. *Reviews of Modern Physics*, **2013**, 85, 961-1019	40.5	679
330	Possible Spin Polarization in a One-Dimensional Electron Gas. *Physical Review Letters*, **1996**, 77, 135-138	7.4	608
329	A single-atom transistor. *Nature Nanotechnology*, **2012**, 7, 242-6	28.7	587
328	Atomically precise placement of single dopants in si. *Physical Review Letters*, **2003**, 91, 136104	7.4	283
327	Ohm's law survives to the atomic scale. *Science*, **2012**, 335, 64-7	33.3	246
326	Metal-Insulator Transition at B=0 in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. *Physical Review Letters*, **1998**, 80, 1292-1295	7.4	219
325	Interaction effects in a one-dimensional constriction. *Physical Review B*, **1998**, 58, 4846-4852	3.3	209
324	Spin-triplet negatively charged excitons in GaAs quantum wells. *Physical Review B*, **1995**, 52, 7841-7844	3.3	157
323	Spectroscopy of few-electron single-crystal silicon quantum dots. *Nature Nanotechnology*, **2010**, 5, 502-5	28.7	140
322	A surface code quantum computer in silicon. *Science Advances*, **2015**, 1, e1500707	14.3	137
321	Toward Atomic-Scale Device Fabrication in Silicon Using Scanning Probe Microscopy. *Nano Letters*, **2004**, 4, 1969-1973	11.5	128
320	A two-qubit gate between phosphorus donor electrons in silicon. *Nature*, **2019**, 571, 371-375	50.4	113
319	Quenching of excitonic optical transitions by excess electrons in GaAs quantum wells. *Physical Review B*, **1995**, 51, 18049-18052	3.3	107
318	Precession and motional slowing of spin evolution in a high mobility two-dimensional electron gas. *Physical Review Letters*, **2002**, 89, 236601	7.4	101
317	Magnetization and Energy Gaps of a High-Mobility 2D Electron Gas in the Quantum Limit. *Physical Review Letters*, **1997**, 79, 3238-3241	7.4	92
316	Atomic-scale, all epitaxial in-plane gated donor quantum dot in silicon. *Nano Letters*, **2009**, 9, 707-10	11.5	90
315	Weak localization, hole-hole interactions, and the "Metal"-insulator transition in two dimensions. *Physical Review Letters*, **2000**, 84, 2489-92	7.4	90

314	Spin blockade and exchange in Coulomb-confined silicon double quantum dots. *Nature Nanotechnology*, **2014**, 9, 430-5	28.7	89
313	Realization of atomically controlled dopant devices in silicon. *Small*, **2007**, 3, 563-7	11	87
312	Encapsulation of phosphorus dopants in silicon for the fabrication of a quantum computer. *Applied Physics Letters*, **2002**, 81, 3197-3199	3.4	83
311	Hole-hole interaction effect in the conductance of the two-dimensional hole gas in the ballistic regime. *Physical Review Letters*, **2002**, 89, 076406	7.4	81
310	Thermometer for the 2D Electron Gas using 1D Thermopower. *Physical Review Letters*, **1998**, 81, 3491-3494	7.4	79
309	Zeeman splitting in ballistic hole quantum wires. *Physical Review Letters*, **2006**, 97, 026403	7.4	75
308	Observation of charge transport by negatively charged excitons. *Science*, **2001**, 294, 837-9	33.3	75
307	Spin readout and addressability of phosphorus-donor clusters in silicon. *Nature Communications*, **2013**, 4, 2017	17.4	74
306	Fano factor reduction on the 0.7 conductance structure of a ballistic one-dimensional wire. *Physical Review Letters*, **2004**, 93, 116602	7.4	72
305	Interaction effects at crossings of spin-polarized one-dimensional subbands. *Physical Review Letters* , **2003**, 91, 136404	7.4	71
304	Ballistic transport in one-dimensional constrictions formed in deep two-dimensional electron gases. *Applied Physics Letters*, **1995**, 67, 109-111	3.4	71
303	Spatially resolving valley quantum interference of a donor in silicon. *Nature Materials*, **2014**, 13, 605-10	27	68
302	Controlled wave-function mixing in strongly coupled one-dimensional wires. *Physical Review B*, **1999**, 59, 12252-12255	3.3	66
301	Detection of Coulomb Charging around an Antidot in the Quantum Hall Regime. *Physical Review Letters*, **1999**, 83, 160-163	7.4	62
300	Phosphine dissociation on the Si(001) surface. *Physical Review Letters*, **2004**, 93, 226102	7.4	58
299	Reentrant Insulator-Metal-Insulator Transition at B=0 in a Two-Dimensional Hole Gas. *Physical Review Letters*, **1999**, 82, 1542-1545	7.4	58
298	Influence of excess electrons and magnetic fields on Mott-Wannier excitons in GaAs quantum wells. *Advances in Physics*, **1995**, 44, 47-72	18.4	57
297	Kondo effect from a tunable bound state within a quantum wire. *Physical Review Letters*, **2008**, 100, 026807	7.4	54

296	Quantum simulation of the Hubbard model with dopant atoms in silicon. *Nature Communications*, **2016**, 7, 11342	17.4	54
295	On the acoustoelectric current in a one-dimensional channel. *Journal of Physics Condensed Matter*, **1996**, 8, L337-L343	1.8	52
294	Angle-resolved Raman spectroscopy of the collective modes in an electron bilayer. *Physical Review B*, **1999**, 59, 2095-2101	3.3	51
293	Fabrication of high-quality one- and two-dimensional electron gases in undoped GaAs/AlGaAs heterostructures. *Applied Physics Letters*, **1999**, 74, 2328-2330	3.4	51
292	A complete fabrication route for atomic-scale, donor-based devices in single-crystal germanium. *Nano Letters*, **2011**, 11, 2272-9	11.5	50
291	Spin-dependent transport in a quasiballistic quantum wire. *Physical Review B*, **2000**, 61, 9952-9955	3.3	50
290	Magnetization Instability in a Two-Dimensional System. *Physical Review Letters*, **1997**, 79, 4449-4452	7.4	49
289	Progress in silicon-based quantum computing. *Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences*, **2003**, 361, 1451-71	3	49
288	Experimental Evidence for Coulomb Charging Effects in an Open Quantum Dot at Zero Magnetic Field. *Physical Review Letters*, **1998**, 81, 3507-3510	7.4	49
287	Thermodynamic density of states of two-dimensional GaAs systems near the apparent metal-insulator transition. *Physical Review Letters*, **2006**, 96, 216407	7.4	47
286	Imaging cyclotron orbits and scattering sites in a high-mobility two-dimensional electron gas. *Physical Review B*, **2000**, 62, 5174-5178	3.3	47
285	Measurement of phosphorus segregation in silicon at the atomic scale using scanning tunneling microscopy. *Applied Physics Letters*, **2004**, 85, 1359-1361	3.4	46
284	Weak localization in high-quality two-dimensional systems. *Physical Review B*, **2004**, 70,	3.3	46
283	Effect of spatial dispersion on acoustoelectric current in a high-mobility two-dimensional electron gas. *Physical Review B*, **1995**, 51, 14770-14773	3.3	46
282	Ultradense phosphorus in germanium delta-doped layers. *Applied Physics Letters*, **2009**, 94, 162106	3.4	45
281	Influence of doping density on electronic transport in degenerate Si:P □doped layers. *Physical Review B*, **2006**, 73,	3.3	45
280	Thermal dissociation and desorption of PH3 on Si(001): A reinterpretation of spectroscopic data. *Physical Review B*, **2006**, 74,	3.3	44
279	Scanning probe microscopy for silicon device fabrication. *Molecular Simulation*, **2005**, 31, 505-515	2	42

278	Exploring the limits of N-type ultra-shallow junction formation. *ACS Nano*, **2013**, 7, 5499-505	16.7	40
277	Magnetization measurements of high-mobility two-dimensional electron gases. *Physical Review B*, **2003**, 67,	3.3	40
276	Two-electron spin correlations in precision placed donors in silicon. *Nature Communications*, **2018**, 9, 980	17.4	39
275	Effect of encapsulation temperature on Si:P δ-doped layers. *Applied Physics Letters*, **2004**, 85, 4953-4955	3.4	39
274	New avenues to an old material: controlled nanoscale doping of germanium. *Nanoscale*, **2013**, 5, 2600-15	7.7	38
273	Phosphine adsorption and dissociation on the Si(001) surface: An ab initio survey of structures. *Physical Review B*, **2005**, 72,	3.3	38
272	Spin read-out in atomic qubits in an all-epitaxial three-dimensional transistor. *Nature Nanotechnology*, **2019**, 14, 137-140	28.7	38
271	Spatial metrology of dopants in silicon with exact lattice site precision. *Nature Nanotechnology*, **2016**, 11, 763-8	28.7	37
270	High-Fidelity Rapid Initialization and Read-Out of an Electron Spin via the Single Donor D(-) Charge State. *Physical Review Letters*, **2015**, 115, 166806	7.4	37
269	Charge sensing of precisely positioned p donors in Si. *Nano Letters*, **2011**, 11, 4376-81	11.5	37
268	Conductance quantization and the 0.7×2e2/h conductance anomaly in one-dimensional hole systems. *Applied Physics Letters*, **2006**, 88, 012107	3.4	37
267	Radio frequency measurements of tunnel couplings and singlet-triplet spin states in Si:P quantum dots. *Nature Communications*, **2015**, 6, 8848	17.4	36
266	Investigating the regrowth surface of Si:P δ-layers toward vertically stacked three dimensional devices. *Applied Physics Letters*, **2009**, 95, 233111	3.4	36
265	Coulomb blockade of tunneling through compressible rings formed around an antidot: An explanation for h/2e Aharonov-Bohm oscillations. *Physical Review B*, **2000**, 62, R4817-R4820	3.3	36
264	Fabrication and transport properties of clean long one-dimensional quantum wires formed in modulation-doped GaAs/AlGaAs heterostructures. *Applied Physics Letters*, **1999**, 75, 2975-2977	3.4	36
263	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. *Nature Physics*, **2008**, 4, 55-59	16.2	35
262	Electron-electron interactions in highly disordered two-dimensional systems. *Physical Review B*, **2008**, 77,	3.3	35
261	Kondo effect in a quantum antidot. *Physical Review Letters*, **2002**, 89, 226803	7.4	35

260	Rapid radiative decay of charged excitons. *Physical Review B*, **2000**, 62, R13294-R13297	3.3	35
259	Negatively charged excitons in coupled double quantum wells. *Physical Review B*, **1997**, 55, 1318-1321	3.3	34
258	STM characterization of the Si-P heterodimer. *Physical Review B*, **2004**, 69,	3.3	34
257	Temperature-dependent Landau damping of the acoustic plasmon in a bilayer system. *Physical Review B*, **1998**, 57, R2065-R2068	3.3	34
256	Fermi-liquid behavior of the low-density 2D hole gas in a GaAs/AlGaAs heterostructure at large values of r(s). *Physical Review Letters*, **2001**, 86, 4895-8	7.4	33
255	Atomically engineered electron spin lifetimes of 30 s in silicon. *Science Advances*, **2017**, 3, e1602811	14.3	32
254	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. *Physical Review B*, **2007**, 75,	3.3	32
253	One-dimensional conduction properties of highly phosphorus-doped planar nanowires patterned by scanning probe microscopy. *Physical Review B*, **2007**, 76,	3.3	32
252	Highly tunable exchange in donor qubits in silicon. *Npj Quantum Information*, **2016**, 2,	8.6	31
251	Imaging charged defects on clean Si(100)-(2□) with scanning tunneling microscopy. *Journal of Applied Physics*, **2002**, 92, 820-824	2.5	30
250	The Aharonov-Bohm effect in the fractional quantum Hall regime. *Surface Science*, **1996**, 361-362, 17-21	1.8	30
249	Suppressing Segregation in Highly Phosphorus Doped Silicon Monolayers. *ACS Nano*, **2015**, 9, 12537-41	16.7	29
248	Electronic structure of realistically extended atomistically resolved disordered Si:P □doped layers. *Physical Review B*, **2011**, 84,	3.3	28
247	Single hydrogen atoms on the Si(001) surface. *Physical Review B*, **2007**, 76,	3.3	28
246	Electronic properties of atomically abrupt tunnel junctions in silicon. *Physical Review B*, **2007**, 75,	3.3	28
245	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. *Physical Review B*, **2004**, 70,	3.3	28
244	Experimental study of the acoustoelectric effects in GaAs-AlGaAs heterostructures. *Journal of Physics Condensed Matter*, **1995**, 7, 7675-7685	1.8	28
243	Microscopic four-point-probe resistivity measurements of shallow, high density doping layers in silicon. *Applied Physics Letters*, **2012**, 101, 262105	3.4	27

242	Resonant Rayleigh scattering by excitonic states laterally confined in the interface roughnessof GaAs/AlxGa1□As single quantum wells. *Physical Review B*, **1997**, 55, 13752-13760	3.3	27
241	Metallic behavior in dilute two-dimensional hole systems. *Physical Review Letters*, **2001**, 87, 126802	7.4	27
240	Single-Shot Single-Gate rf Spin Readout in Silicon. *Physical Review X*, **2018**, 8,	9.1	27
239	Engineering independent electrostatic control of atomic-scale (~4 nm) silicon double quantum dots. *Nano Letters*, **2012**, 12, 4001-6	11.5	26
238	0.7 Structure and zero bias anomaly in ballistic hole quantum wires. *Physical Review Letters*, **2008**, 100, 016403	7.4	26
237	Scanning tunneling microscope based fabrication of nano- and atomic scale dopant devices in silicon: The crucial step of hydrogen removal. *Journal of Applied Physics*, **2007**, 101, 034305	2.5	26
236	Excitonic recombination processes in spin-polarized two-dimensional electron gases. *Physical Review B*, **1998**, 58, R4227-R4230	3.3	26
235	Phosphorus atomic layer doping of germanium by the stacking of multiple □layers. *Nanotechnology* , **2011**, 22, 375203	3.4	25
234	Fabrication of induced two-dimensional hole systems on (311)A GaAs. *Journal of Applied Physics*, **2006**, 99, 023707	2.5	25
233	Atomic-scale patterning of hydrogen terminated Ge(001) by scanning tunneling microscopy. *Nanotechnology*, **2009**, 20, 495302	3.4	24
232	Fabrication of high mobility in situ back-gated (311)A hole gas heterojunctions. *Applied Physics Letters*, **1997**, 70, 2750-2752	3.4	24
231	Phosphine dissociation and diffusion on Si(001) observed at the atomic scale. *Journal of Physical Chemistry B*, **2006**, 110, 3173-9	3.4	24
230	Imaging diffraction-limited electronic collimation from a non-equilibrium one-dimensional ballistic constriction. *Journal of Physics Condensed Matter*, **2000**, 12, L167-L172	1.8	24
229	One-dimensional probability density observed using scanned gate microscopy. *Journal of Physics Condensed Matter*, **2000**, 12, L735-L740	1.8	24
228	Phase coherence, interference, and conductance quantization in a confined two-dimensional hole gas. *Physical Review B*, **1994**, 49, 5101-5104	3.3	24
227	High-Fidelity Single-Shot Singlet-Triplet Readout of Precision-Placed Donors in Silicon. *Physical Review Letters*, **2017**, 119, 046802	7.4	23
226	Phosphorus molecules on Ge(001): a playground for controlled n-doping of germanium at high densities. *ACS Nano*, **2013**, 7, 11310-6	16.7	23
225	Comparison of optical and transport measurements of electron densities in quantum wells. *Semiconductor Science and Technology*, **1996**, 11, 890-896	1.8	23

224	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. *Nanotechnology*, **2007**, 18, 044023	3.4	23
223	Towards the atomic-scale fabrication of a silicon-based solid state quantum computer. *Surface Science*, **2003**, 532-535, 1209-1218	1.8	23
222	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. *Nanotechnology*, **2005**, 16, 2446-9	3.4	23
221	Reaction paths of phosphine dissociation on silicon (001). *Journal of Chemical Physics*, **2016**, 144, 014705	3.9	23
220	Split-off dimer defects on the Si(001)2□1 surface. *Physical Review B*, **2004**, 69,	3.3	22
219	Origin of the oscillator strength of the triplet state of a trion in a magnetic field. *Physical Review Letters*, **2002**, 89, 246805	7.4	22
218	Transport in asymmetrically coupled donor-based silicon triple quantum dots. *Nano Letters*, **2014**, 14, 1830-5	11.5	21
217	Epitaxial top-gated atomic-scale silicon wire in a three-dimensional architecture. *Nanotechnology*, **2013**, 24, 045303	3.4	21
216	Direct measurement of the band structure of a buried two-dimensional electron gas. *Physical Review Letters*, **2013**, 110, 136801	7.4	21
215	Influence of encapsulation temperature on Ge:P □doped layers. *Physical Review B*, **2009**, 80,	3.3	21
214	Radio frequency reflectometry and charge sensing of a precision placed donor in silicon. *Applied Physics Letters*, **2015**, 107, 093504	3.4	20
213	Low resistivity, super-saturation phosphorus-in-silicon monolayer doping. *Applied Physics Letters*, **2014**, 104, 123502	3.4	20
212	Quantum-dot electron occupancy controlled by a charged scanning probe. *Physical Review B*, **2002**, 66,	3.3	20
211	Spin-dependent transport in a clean one-dimensional channel. *Physical Review B*, **1999**, 60, 10687-10690	3.3	20
210	Limits to metallic conduction in atomic-scale quasi-one-dimensional silicon wires. *Physical Review Letters*, **2014**, 113, 246802	7.4	19
209	Effective mass theory of monolayer □doping in the high-density limit. *Physical Review B*, **2012**, 85,	3.3	19
208	Phosphorus and hydrogen atoms on the (0 0 1) surface of silicon: A comparative scanning tunnelling microscopy study of surface species with a single dangling bond. *Surface Science*, **2006**, 600, 318-324	1.8	19
207	Bottom-up assembly of metallic germanium. *Scientific Reports*, **2015**, 5, 12948	4.9	18

206	Surface gate and contact alignment for buried, atomically precise scanning tunneling microscopy-patterned devices. *Journal of Vacuum Science & Technology B*, **2007**, 25, 2562		18
205	STM imaging of buried P atoms in hydrogen-terminated Si for the fabrication of a Si:P quantum computer. *Thin Solid Films*, **2004**, 464-465, 23-27	2.2	18
204	Nonlinear transport in a single-mode one-dimensional electron gas. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1998**, 77, 1213-1218		18
203	High-Sensitivity Charge Detection with a Single-Lead Quantum Dot for Scalable Quantum Computation. *Physical Review Applied*, **2016**, 6,	4.3	17
202	Stacking of 2D electron gases in Ge probed at the atomic level and its correlation to low-temperature magnetotransport. *Nano Letters*, **2012**, 12, 4953-9	11.5	17
201	Metal-insulator transition at B=0 in an ultra-low density two-dimensional hole gas. *Physica B: Condensed Matter*, **1998**, 249-251, 705-709	2.8	17
200	Compressibility studies of double electron and double hole gas systems. *Applied Physics Letters*, **1996**, 68, 3323-3325	3.4	17
199	Experimental investigation of the damping of low-frequency edge magnetoplasmons in GaAs-AlxGa1-xAs heterostructures. *Physical Review B*, **1994**, 50, 1582-1587	3.3	17
198	The Impact of Dopant Segregation on the Maximum Carrier Density in Si:P Multilayers. *ACS Nano*, **2015**, 9, 7080-4	16.7	16
197	Transport through a single donor in p-type silicon. *Applied Physics Letters*, **2013**, 103, 043106	3.4	16
196	Atomistic modeling of metallic nanowires in silicon. *Nanoscale*, **2013**, 5, 8666-74	7.7	16
195	n-type doping of germanium from phosphine: early stages resolved at the atomic level. *Physical Review Letters*, **2012**, 109, 076101	7.4	16
194	Atomic layer doping of strained Ge-on-insulator thin films with high electron densities. *Applied Physics Letters*, **2013**, 102, 151103	3.4	16
193	Electrical Characterization of Ordered Si:P Dopant Arrays. *IEEE Nanotechnology Magazine*, **2007**, 6, 213-217	1.6	16
192	Coulomb charging effects in an open quantum dot device. *Journal of Physics Condensed Matter*, **2001**, 13, 9515-9534	1.8	16
191	Addressable electron spin resonance using donors and donor molecules in silicon. *Science Advances*, **2018**, 4, eaaq1459	14.3	15
190	Spin-lattice relaxation times of single donors and donor clusters in silicon. *Physical Review Letters*, **2014**, 113, 246406	7.4	15
189	Interplay between quantum confinement and dielectric mismatch for ultrashallow dopants. *Physical Review B*, **2013**, 87,	3.3	15

188	Anomalous spin-dependent behavior of one-dimensional subbands. *Physical Review B*, **2005**, 72,	3.3	15
187	Electron Density Dependence of the Excitonic Absorption Thresholds of GaAs Quantum Wells. *Physica Status Solidi A*, **2000**, 178, 465-470		15
186	Engineering long spin coherence times of spin-orbit qubits in silicon. *Nature Materials*, **2021**, 20, 38-42	27	15
185	Ultralow-Noise Atomic-Scale Structures for Quantum Circuitry in Silicon. *Nano Letters*, **2016**, 16, 5779-84	11.5	14
184	Spontaneous breaking of time-reversal symmetry in strongly interacting two-dimensional electron layers in silicon and germanium. *Physical Review Letters*, **2014**, 112, 236602	7.4	14
183	Probing the Quantum States of a Single Atom Transistor at Microwave Frequencies. *ACS Nano*, **2017**, 11, 2444-2451	16.7	14
182	Suppression of low-frequency noise in two-dimensional electron gas at degenerately doped Si:P □ layers. *Physical Review B*, **2011**, 83,	3.3	14
181	Optimizing dopant activation in Si:P double □layers. *Journal of Crystal Growth*, **2010**, 312, 3247-3250	1.6	14
180	Investigating the surface quality and confinement of Si:P □layers at different growth temperatures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1180-1183	3	14
179	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. *Physical Review B*, **2008**, 77,	3.3	14
178	STM investigation of epitaxial Si growth for the fabrication of a Si-based quantum computer. *Applied Surface Science*, **2003**, 212-213, 319-324	6.7	14
177	Evolution of the bilayer □1 quantum Hall state under charge imbalance. *Physical Review B*, **2005**, 71,	3.3	14
176	Electron correlations in an electron bilayer at finite temperature: Landau damping of the acoustic plasmon. *Journal of Physics Condensed Matter*, **2000**, 12, 439-466	1.8	14
175	Readout and control of the spin-orbit states of two coupled acceptor atoms in a silicon transistor. *Science Advances*, **2018**, 4, eaat9199	14.3	14
174	Importance of charging in atomic resolution scanning tunneling microscopy: Study of a single phosphorus atom in a Si(001) surface. *Physical Review B*, **2006**, 74,	3.3	13
173	Localisation and the metal□nsulator transition in two dimensions. *Physica B: Condensed Matter*, **2001**, 296, 21-31	2.8	13
172	Tuning the electron transport properties of a one-dimensional constriction using hydrostatic pressure. *Physical Review B*, **2002**, 65,	3.3	13
171	Multilayered gated lateral quantum dot devices. *Applied Physics Letters*, **2000**, 76, 1134-1136	3.4	13

170	Tunneling Statistics for Analysis of Spin-Readout Fidelity. *Physical Review Applied*, **2017**, 8,	4.3	12
169	Strain and electric field control of hyperfine interactions for donor spin qubits in silicon. *Physical Review B*, **2015**, 91,	3.3	12
168	Development of a tunable donor quantum dot in silicon. *Applied Physics Letters*, **2010**, 96, 043116	3.4	12
167	Enhancing electron transport in Si:P delta-doped devices by rapid thermal anneal. *Applied Physics Letters*, **2008**, 93, 142105	3.4	12
166	Exploiting a Single-Crystal Environment to Minimize the Charge Noise on Qubits in Silicon. *Advanced Materials*, **2020**, 32, e2003361	24	12
165	A tight-binding study of single-atom transistors. *Small*, **2015**, 11, 374-81	11	11
164	Two-electron states of a group-V donor in silicon from atomistic full configuration interactions. *Physical Review B*, **2018**, 97,	3.3	11
163	Valley splitting in a silicon quantum device platform. *Nano Letters*, **2014**, 14, 1515-9	11.5	11
162	Single-charge detection by an atomic precision tunnel junction. *Applied Physics Letters*, **2014**, 104, 113113	3.4	11
161	Lithography and doping in strained Si towards atomically precise device fabrication. *Nanotechnology*, **2014**, 25, 145302	3.4	11
160	Effect of finite quantum-well width on the compressibility of a two-dimensional electron gas. *Physical Review B*, **1997**, 55, 6715-6718	3.3	11
159	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. *Applied Physics Letters*, **2008**, 92, 052101	3.4	11
158	Interface-induced heavy-hole/light-hole splitting of acceptors in silicon. *Applied Physics Letters*, **2015**, 106, 203110	3.4	10
157	Manifestation of a non-Abelian Berry phase in a p-type semiconductor system. *Physical Review B*, **2016**, 93,	3.3	10
156	Dual-temperature encapsulation of phosphorus in germanium layers toward ultra-shallow junctions. *Journal of Crystal Growth*, **2011**, 316, 81-84	1.6	10
155	First-principles modelling of scanning tunneling microscopy using non-equilibrium Green functions. *Frontiers of Physics in China*, **2010**, 5, 369-379		10
154	Radio-frequency reflectometry on large gated two-dimensional systems. *Review of Scientific Instruments*, **2008**, 79, 123901	1.7	10
153	Doping and STM tip-induced changes to single dangling bonds on Si(0 0 1). *Surface Science*, **2007**, 601, 4036-4040	1.8	10

152	The effect of surface proximity on electron transport through ultra-shallow -doped layers in silicon. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1566-1568	3	10
151	Scanning tunneling microscopy imaging of charged defects on clean Si(100)-(2□1). *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2003**, 21, 1506-1509	2.9	10
150	Optical imaging of trion diffusion and drift in GaAs quantum wells. *Physical Review B*, **2003**, 68,	3.3	10
149	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. *Physical Review B*, **2005**, 72,	3.3	10
148	Effective removal of hydrogen resists used to pattern devices in silicon using scanning tunneling microscopy. *Applied Physics Letters*, **2005**, 86, 143116	3.4	10
147	Formation and Recombination Dynamics of Charged Excitons in a GaAs Quantum Well. *Physica Status Solidi (B): Basic Research*, **2001**, 227, 297-306	1.3	10
146	Non-equilibrium transport along an edge of variable slope in the fractional quantum Hall regime. *Physica B: Condensed Matter*, **1998**, 249-251, 405-409	2.8	9
145	Skyrmion□hole excitations at □1 studied by photoluminescence spectroscopy. *Physica B: Condensed Matter*, **1998**, 249-251, 544-548	2.8	9
144	Huge positive magnetoresistance of GaAs□AlGaAs high electron mobility transistor structures at high temperatures. *Applied Physics Letters*, **2007**, 90, 252106	3.4	9
143	0.7 Analogue structures and exchange interactions in quantum wires. *Solid State Communications*, **2004**, 131, 591-597	1.6	9
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140	Spin□rbit coupling in silicon for electrons bound to donors. *Npj Quantum Information*, **2018**, 4,	8.6	9
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137	Impact of nuclear spin dynamics on electron transport through donors. *Physical Review B*, **2015**, 92,	3.3	8
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